



Full Length Article

Comparison of performance and optoelectronic processes in ZnO and TiO₂ nanorod array-based hybrid solar cells



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ABSTRACT

The reported efficiencies of pristine ZnO nanorod array (NRA)-based polymer-inorganic hybrid solar cells (HSCs) are normally lower than those of their pristine TiO₂ NRA-based counterparts. This difference typically results from the lower short-circuit current density (J_{sc}) of the ZnO NRA device. This paper presents a comparative study of pristine ZnO and TiO₂ NRA-based HSCs. We investigate the morphological structure (length, diameter, number density, area of nanorod laterals), photovoltaic performance (current density-voltage $J-V$, external quantum efficiency EQE), and optoelectronic processes related to electron transfer (electron mobility μ_e , electron diffusion length L_D , electron lifetime τ_e and electron transit time τ_t related electron collecting efficiency η_{cc} , electron injection η_{inj} , surface potential SP, photoluminescence PL, bound charge pairs BCP) in HSCs, with ZnO and TiO₂ NRA as electron acceptor. Our comparative investigations reveal that the factors relating to the interface area, μ_e , L_D , and η_{cc} are not the key factors responsible for the difference in the value of J_{sc} in ZnO and TiO₂ NRA-based HSCs with the same device structure. In fact, the crucial step for a lower J_{sc} in ZnO NRA-based HSCs than in TiO₂ NRA-based HSCs is attributed to the less efficient transfer of photo-generated electrons at the charge separation interface in ZnO NRA-based HSCs. Dynamic characterizations indicate that the transfer of interfacial photo-generated electrons in TiO₂ NRA-based HSCs is more efficient than ZnO NRA-based HSCs, and is confirmed by Kelvin probe force microscopy (KPFM) and PL studies. The reason for the better interface charge transfer property in MEH-PPV/TiO₂ NRA than that of in MEH-PPV/ZnO NRA is further investigated by Marcus model, we find that more trapped BCP states are generated in the ZnO NRA based HSCs, which resulting in lower interfacial electron injection efficiency from polymer to ZnO NRA.

1. Introduction

Polymer-inorganic hybrid solar cells (HSCs) based on a conjugated polymer as the donor (D) and inorganic semiconductor nanocrystals as the acceptor (A) in a bulk heterojunction structure are interesting and promising for photovoltaic energy conversion owing to their advantages of being low-cost, simple fabrication by processing from solution, and the fact that they can be used to fabricate flexible devices [1,2]. A material comprising a combination of ZnO and TiO₂ is attractive for nanoscale optoelectronic devices, because it is a wide band gap semiconductor with good carrier mobility [3]. A promising photovoltaic device architecture consisting of direct and ordered electron transport pathways formed by an ZnO and TiO₂ nanorod array (NRA) instead of the disordered channels provided by nanoparticles has been proposed [4,5], as shown in Fig. 1.

The band gap of ZnO is similar to that of TiO₂, and the conduction band edge of both materials is located at approximately the same level [3–5]. However, the electron mobility exhibited by ZnO NRA is orders of magnitudes higher than that of TiO₂ NRA [6–8], which suggests that ZnO NRA-based HSCs should have superior performance. Table 1 lists some performance properties recently reported for pristine ZnO and TiO₂ NRA-based HSCs without any interfacial modification or fullerene incorporated in the polymer. Interestingly, most of the efficiencies reported for the pristine ZnO NRA-based solar cells (0.02–0.76%) [9–20] are normally lower than those of pristine TiO₂ NRA-based solar cells (0.21–1.74%) [21–29], which is generally a consequence of the higher short-circuit current density J_{sc} in a TiO₂ NRA device (1.47–5.15 mA/cm²) compared to its pristine ZnO NRA counterpart (0.52–3.20 mA/cm²).

In fact, a similar phenomenon has also been observed in dye-

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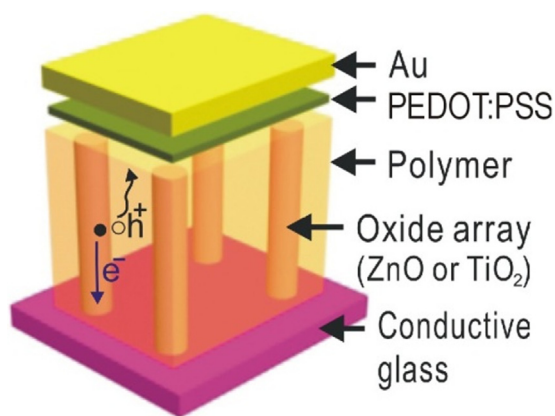


Fig. 1. Architecture of polymer/oxide array HSCs. The arrows show the electron (e^- , solid point) and hole (h^+ , empty circle) transportation.

Table 1

Recently reported performance of HSCs based on pristine ZnO and TiO_2 NRA without any interfacial modification or fullerene incorporated in the polymer.

	Polymer	Year	V_{oc} (V)	J_{sc} (mA/cm ²)	FF	PCE (%)	Ref
ZnO NRA	P3HT	2011	0.54	2.67	0.53	0.76	[9]
	P3HT	2012	0.37	3.19	0.41	0.48	[10]
	MEH-PPV	2013	0.36	1.22	0.33	0.15	[11]
	P3HT	2013	0.32	0.66	0.53	0.11	[12]
	P3HT	2013	0.32	3.20	0.53	0.54	[13]
	P3HT	2014	0.41	1.02	0.35	0.15	[14]
	P3HT	2015	0.26	1.41	0.41	0.10	[15]
	MEH-PPV	2015	0.35	1.48	0.33	0.17	[16]
	P3HT	2016	0.42	0.75	0.49	0.16	[17]
	P3HT	2016	0.38	0.86	0.33	0.11	[18]
	P3HT	2017	0.30	1.11	0.42	0.14	[19]
	P3HT	2018	0.11	0.52	0.28	0.02	[20]
	TiO_2 NRA	P3HT	2008	0.32	3.89	0.41	0.51
P3HT		2012	0.40	2.01	0.55	0.43	[22]
P3HT		2013	0.39	1.47	0.38	0.22	[23]
P3HT		2013	0.36	2.18	0.38	0.30	[24]
MEH-PPV		2014	0.34	3.48	0.33	0.39	[25]
P3HT		2015	0.65	5.15	0.52	1.74	[26]
MEH-PPV		2015	0.38	2.19	0.33	0.27	[27]
P3HT		2016	0.33	1.66	0.39	0.21	[28]
PCPDTBT		2017	0.62	4.10	0.43	1.10	[29]

sensitized solar cells (DSCs), and the lower photocurrent of ZnO NRA-based DSCs has been ascribed to the partial dissolution of the ZnO surface and formation of dye aggregates [30,31]. However, the interface destruction and dye aggregates do not exist in HSCs because of the use of moderated conjugated polymer instead of dye. Therefore, it needs to be clear which processes are responsible for the weaker photocurrent in ZnO NRA-based HSCs compared to their TiO_2 NRA counterparts. To the best of our knowledge, a study involving a one-to-one comparison of the electron transfer properties of ZnO and TiO_2 NRA-based HSCs to demonstrate that TiO_2 is a superior acceptor for HSCs has not yet been reported. Although the ZnO- TiO_2 core-shell structure array has been studied in HSCs and DSCs [3,32,33], it could not readily be concluded that TiO_2 NRA is a more effective acceptor than ZnO NRA in HSCs. Because they ascribed the improved performance mostly to the passivation of defect states on the ZnO NRA surface and the modified charge separation interface [32,33], rather than the intrinsic property of TiO_2 itself; moreover, the ZnO-ZnO core-shell structure array has also been shown capable of being much more efficient than its pristine ZnO NRA counterpart [34]. Therefore, the ZnO- TiO_2 core-shell study does not provide a credible comparison of the transport properties in pristine ZnO and TiO_2 NRA in HSCs, which are not yet fully understood. The aim of this study is to compare the performance of HSCs fabricated with pristine ZnO and TiO_2 NRA with the aim of identifying the key

electronic process responsible for the observed J_{sc} differences in ZnO and TiO_2 NRA-based HSCs under illumination, such that strategies for the relative improvement of the device can be formulated.

2. Material and methods

2.1. Synthesis of ZnO NRA and TiO_2 NRA

The ZnO NRA was grown by firstly coating a dense ZnO layer onto patterned fluoride-doped tin oxide (FTO) glass ($14 \Omega/\text{sq}$, Huanan Xiangcheng Hi-Tech Co., Ltd., China) by spin-coating (1500 rpm, 60 s) the ZnO precursor solution of zinc acetate (0.327 g) and acetic acid (0.20 mL) in the mixture of 8 mL of anhydrous alcohol and 2 mL of water. The ZnO-NRA was hydrothermally grown by suspending the ZnO-coated FTO conducting glass upside down in an aqueous solution of zinc nitrate hexahydrate (0.025 M) and hexamethylenetetramine (0.025 M) at 90°C for 2 h in an electric oven to produce the ZnO NRA [34–36].

The TiO_2 NRA was hydrothermally grown on FTO-coated glass, following an approach similar to previous work [25,37]. Deionized water was mixed with concentrated hydrochloric acid (35%) (volume ratio:1:1) to reach a total volume of 60 mL in a Teflon-lined stainless steel autoclave (100 mL volume). The mixture was stirred in ambient conditions for 5 min before adding into the Teflon liner, after which the cleaned FTO substrate was inserted upside down in the Teflon liner with the above mixture solution, and 1 mL of titanium (IV) isopropoxide (TTIP, 97%) was added. After 10 min of sonication, the autoclave was sealed and heated at 180°C for 100 min in an electric oven to produce the TiO_2 NRA.

2.2. Device fabrication

MEH-PPV (average $M_n = 40,000$ – $70,000$, Aldrich) and poly(3,4-ethylene dithiophene):poly(styrene-sulfonate) (PEDOT:PSS) (Clevios P HC V4, H. C. Starck) were commercially obtained. The MEH-PPV layer was deposited on top of the oxide array by spin-coating (1000 rpm, 40 s) the MEH-PPV solution in chlorobenzene (10 mg/mL) under ambient conditions. This was followed by annealing at 150°C under N_2 atmosphere for 10 min. Subsequently, a PEDOT:PSS film was spin-coated (2000 rpm, 60 s) over the polymer layer. After the deposition of the PEDOT:PSS, the sample was sequentially heated for 10 min at 100°C in a glove box (N_2). Finally, a gold electrode (100 nm) was evaporated through a shadow mask to form an overlapped area of 0.12 cm^2 between the FTO and Au, which defined the effective device area.

2.3. Characterization and instruments

Scanning electron microscopy (SEM) measurements of the nanostructures, in the form of field-emission scanning electron microscopy (FE-SEM, FEI Sirion200), were carried out. The room-temperature photoluminescence (PL) properties were measured under ambient conditions. PL measurements were performed on a Hitachi F-7000 spectrofluorophotometer. The absorption spectra were recorded with a Shimadzu UV-2600 spectrophotometer. The steady-state J - V curves were measured with AM1.5 illumination under ambient conditions using a 94023A Oriol Sol3A solar simulator (Newport Stratford, Inc.) with a 450-W xenon lamp as the light source. Incident photon-to-current efficiency (IPCE) spectra of the solar cells were measured by using a QE/IPCE measurement kit (Zolix Instruments Co., Ltd.) in the spectral range of 300–900 nm. Intensity modulated photocurrent spectra (IMPS) and Intensity modulated photovoltage spectra (IMVS) spectra were characterized by a controlled intensity modulated photo spectroscopy (CIMPS) (Zahner Co., Germany) in ambient conditions with a blue light emitting diode (LED) as illumination source (background illuminating light intensity is $15.85 \text{ mW}/\text{cm}^2$, and the depth of small sinusoidal

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